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(57) **ABSTRACT**

A semiconductor device includes a substrate including an active pattern, a channel pattern on the active pattern and including semiconductor patterns, a source/drain pattern connected to the semiconductor patterns, a gate electrode on the semiconductor patterns, and a gate dielectric layer between the gate electrode and the semiconductor patterns. An inner spacer of the gate dielectric layer includes a horizontal portion between the high-k dielectric layer and the second semiconductor pattern, a vertical portion between the high-k dielectric layer and the source/drain pattern, and a corner portion between the horizontal portion and the vertical portion. A first thickness of the horizontal portion is less than a second thickness of the vertical portion. The second thickness of the vertical portion is less than a third thickness of the corner portion.

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